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## FDP025N06 N-Channel PowerTrench<sup>®</sup> MOSFET 60 V, 265 A, 2.5 mΩ

## Features

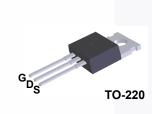
- $R_{DS(on)}$  = 1.9 m $\Omega$  (Typ.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 75 A
- · Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low  $R_{\text{DS}(\text{on})}$
- High Power and Current Handling Capability
- RoHS Compliant

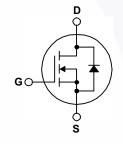
## Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench<sup>®</sup> process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

## Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies
- Renewable system





### MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

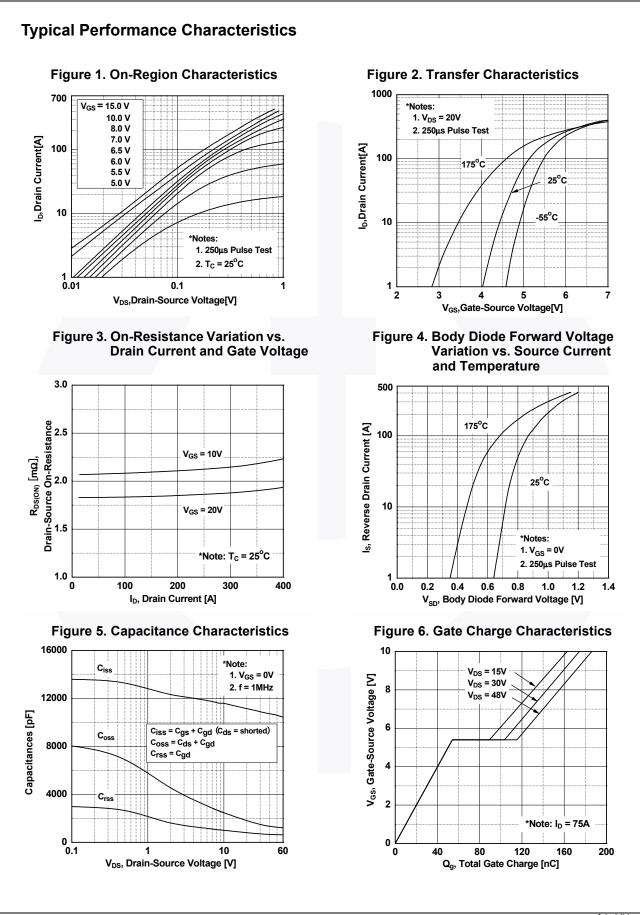
Symbol		Parameter	FDP025N06	Unit	
V <sub>DSS</sub>	Drain to Source Voltage	60	V		
V <sub>GSS</sub>	Gate to Source Voltage		±20	V	
ID		- Continuous (T <sub>C</sub> = 25°C, Silicon Limited)	265		
	Drain Current	- Continuous (T <sub>C</sub> = 100°C, Silicon Limited	l) 190	Α	
		- Continuous (T <sub>C</sub> = 25°C, Package Limite	d) 120		
I <sub>DM</sub>	Drain Current	- Pulsed (Note	1) 1060	А	
E <sub>AS</sub>	Single Pulsed Avalanche Er	2) 2531	mJ		
dv/dt	Peak Diode Recovery dv/dt	3) 6.0	V/ns		
P <sub>D</sub>	Dower Dissinction	(T <sub>C</sub> = 25°C)	395	W	
	Power Dissipation	- Derate Above 25°C	2.6	W/ºC	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Tem	-55 to +175	°C		
TL	Maximum Lead Temperature	e for Soldering, 1/8" from Case for 5 Seconds	300	°C	

## **Thermal Characteristics**

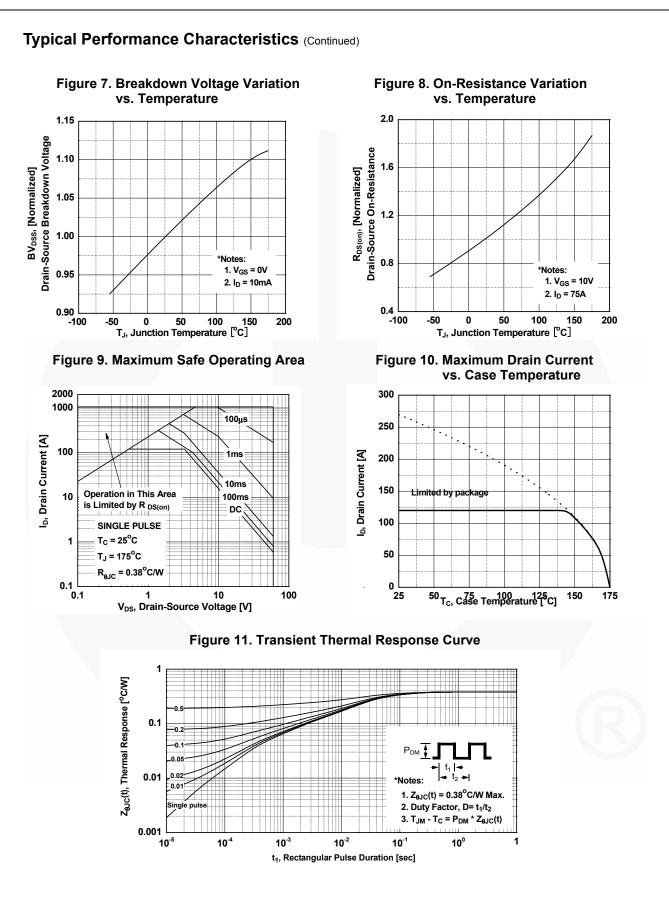
Symbol	Parameter	FDP025N06	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.38	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	0/11

November 2013

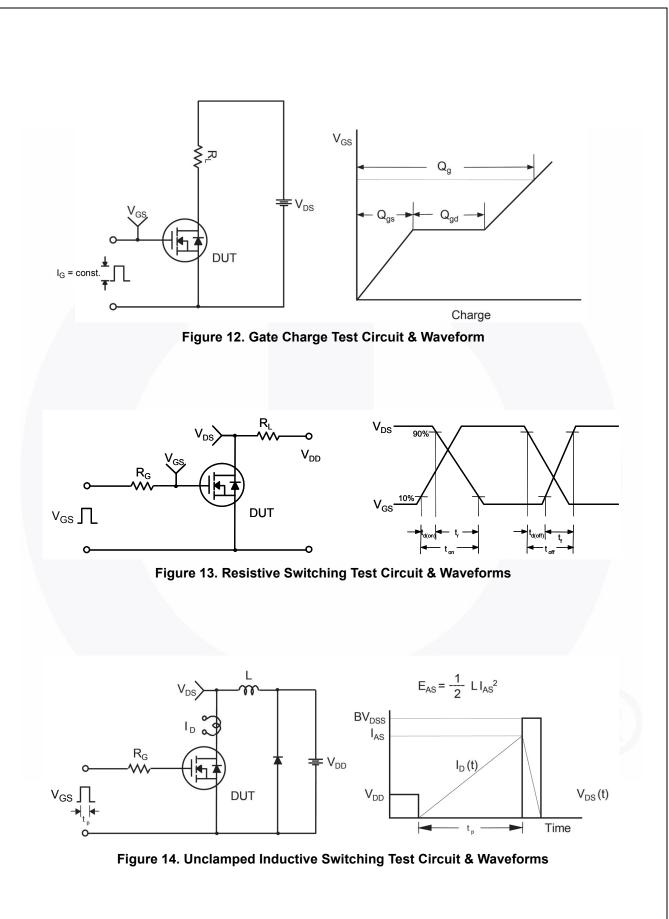
		Packa	ige	Packing Method	Reel Size	) T	ape Width	Qua	antity	
		TO-2			N/A	N/A		50 units		
Electrica	l Char	acteristics T <sub>C</sub> = 2	25°C unles	s othe	erwise noted.					
Symbol		Parameter			Test Condition	S	Min.	Тур.	Max.	Unit
Off Chara	cteristic	S								
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage		tage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V			60	-	-	V
∆BV <sub>DSS</sub>		Breakdown Voltage Temperature		$I_D = 250 \ \mu$ A, Referenced to $25^{\circ}$ C				0.04		N/00
$/\Delta T_J$	Coefficient						-	0.04	-	V/°C
	Zero G	ate Voltage Drain Currer	ht.	$V_{DS}$	= 60 V, V <sub>GS</sub> = 0 V		-	-	1	μA
I <sub>DSS</sub> Zero Gate Voltage Drain Current				= 60 V, V <sub>GS</sub> = 0 V, T	<sub>C</sub> = 150 <sup>o</sup> C	-	-	500	μΛ	
GSS	Gate to	Body Leakage Current		$V_{GS}$	= ±20 V, V <sub>DS</sub> = 0 V		-	-	±100	nA
On Chara	teristic	e								
V <sub>GS(th)</sub>		nreshold Voltage	-	Voo	= V <sub>DS</sub> , I <sub>D</sub> = 250 μA		2.5	3.5	4.5	V
R <sub>DS(on)</sub>		rain to Source On Resis	stance		$= 10 \text{ V}, \text{ I}_{\text{D}} = 75 \text{ A}$		-	1.9	2.5	mΩ
9 <sub>FS</sub>		d Transconductance			= 10 V, I <sub>D</sub> = 75 A		-	200	-	S
				1.02						_
Dynamic (				1						1
C <sub>iss</sub>		apacitance		V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		-	-	11190	14885	pF
C <sub>oss</sub>		Capacitance	_			_	-	1610	2140	pF
C <sub>rss</sub>		e Transfer Capacitance					-	750	1125	pF
Q <sub>g(tot)</sub>		ate Charge at 10V			= 48 V, I <sub>D</sub> = 75 A	-	-	174	226	nC
Q <sub>gs</sub>		Source Gate Charge		V <sub>GS</sub> = 10 V		(Note 4)	-	54	-	nC
Q <sub>gd</sub>	Gate to	Drain "Miller" Charge				(Note 4)	-	50	-	nC
Switching	Charac	teristics								
t <sub>d(on)</sub>	Turn-Or	n Delay Time				-	134	278	ns	
r	Turn-On Rise Time			V <sub>DD</sub> = 30 V, I <sub>D</sub> = 75 A,			-	324	658	ns
t <sub>d(off)</sub>	Turn-Of	f Delay Time		$V_{GS}$ = 10 V, $R_G$ = 25 $\Omega$ (Note 4)		-	348	706	ns	
t <sub>f</sub>	Turn-Of	f Fall Time				•	250	510	ns	
Jrain-Sou	rce Dio	de Characteristics								
	1	m Continuous Drain to S		de Fr	rward Current			-	265	А
I <sub>S</sub> I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode					-	-	1060	A	
V <sub>SD</sub>	Drain to Source Diode Forward Voltage			$V_{GS} = 0 V, I_{SD} = 75 A$		-	-	1.3	V	
rr SD		Recovery Time	vollago	$V_{GS} = 0 V, I_{SD} = 75 A,$			-	69	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge			$v_{GS} = 0 v, i_{SD} = 75 A,$ $dI_{F}/dt = 100 A/\mu s$		-	152		nC	



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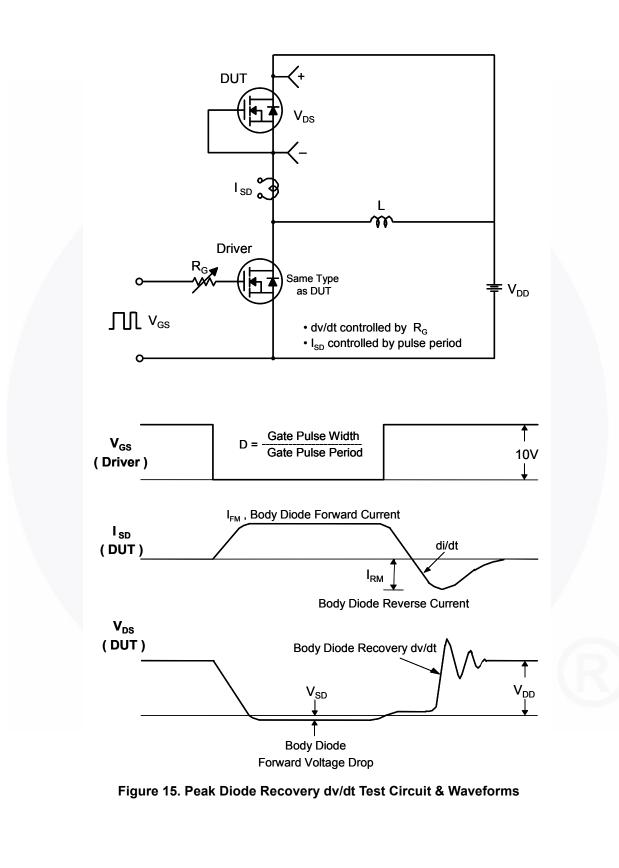


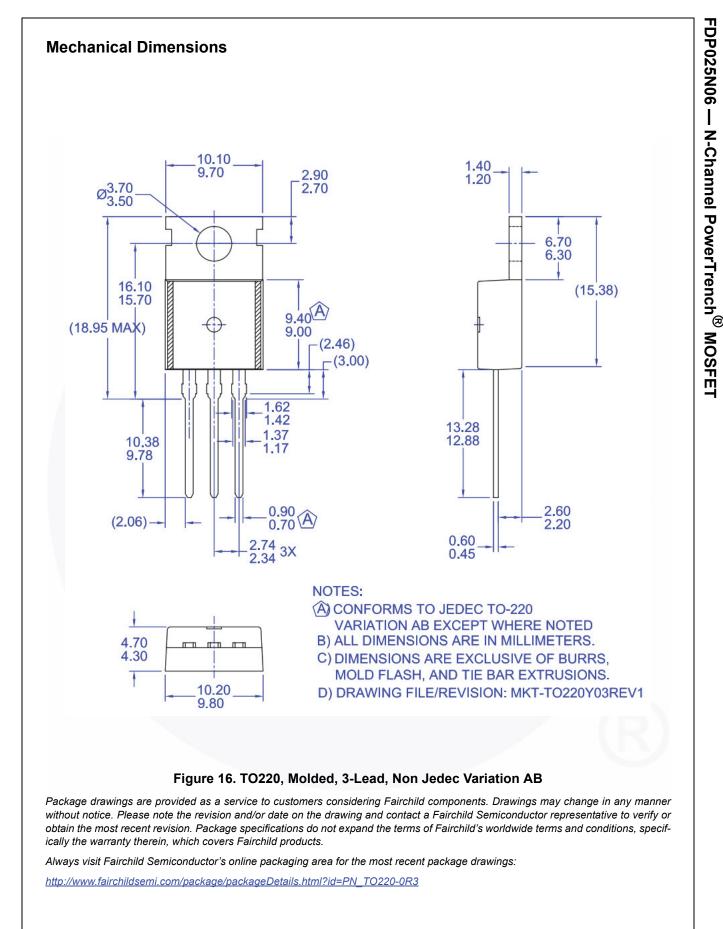
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